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Preferred Devices

## **Complementary NPN-PNP Power Bipolar Transistors**

These complementary devices are lower power versions of the popular MJW3281A and MJW1302A audio output transistors. With superior gain linearity and safe operating area performance, these transistors are ideal for high fidelity audio amplifier output stages and other linear applications.

## Features

- •Exceptional Safe Operating Area
- •NPN/PNP Gain Matching within 10% from 50 mA to 5 A
- •Excellent Gain Linearity
- •High BVCEO
- •High Frequency

#### Benefits

- •Reliable Performance at Higher Powers
- •Symmetrical Characteristics in Complementary Configurations
- •Accurate Reproduction of Input Signal
- •Greater Dynamic Range
- •High Amplifier Bandwith

## Applications

- •High-End Consumer Audio Products
  - ♦Home Amplifiers
  - ♦Home Receivers
- Professional Audio Amplifiers
  - •Theater and Stadium Sound Systems
  - Public Address Systems (PAs)

## MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V <sub>CEO</sub>	260	Vdc
Collector-Base Voltage	V <sub>CBO</sub>	260	Vdc
Emitter-Base Voltage	V <sub>EBO</sub>	5.0	Vdc
Collector-Emitter Voltage - 1.5 V	V <sub>CEX</sub>	260	Vdc
Collector Current – Continuous – Peak (Note 1)	۱ <sub>C</sub>	15 30	Adc
Base Current – Continuous	Ι <sub>Β</sub>	1.5	Adc
Total Power Dissipation @ $T_C = 25^{\circ}C$	PD	150	Watts
Operating and Storage Junction Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	– 65 to +150	°C

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

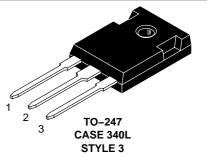
1. Pulse Test: Pulse Width = 5.0 ms, Duty Cycle < 10%.



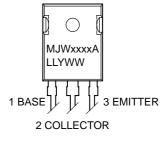
## **ON Semiconductor®**

http://onsemi.com

15 AMPERES COMPLEMENTARY SILICON POWER TRANSISTORS 260 VOLTS 150 WATTS



## MARKING DIAGRAM



MJWxxxxA = Device Code				
XXXX	= 0281 OR 0302			
LL	= Location Code			
Y	= Year			
WW	= Work Week			

## ORDERING INFORMATION

Device	Package	Shipping		
MJW0281A	TO-247	30 Units/Rail		
MJW0302A	TO-247	30 Units/Rail		

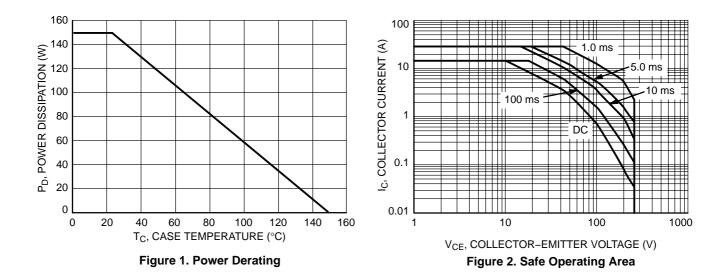
Preferred devices are recommended choices for future use and best overall value.

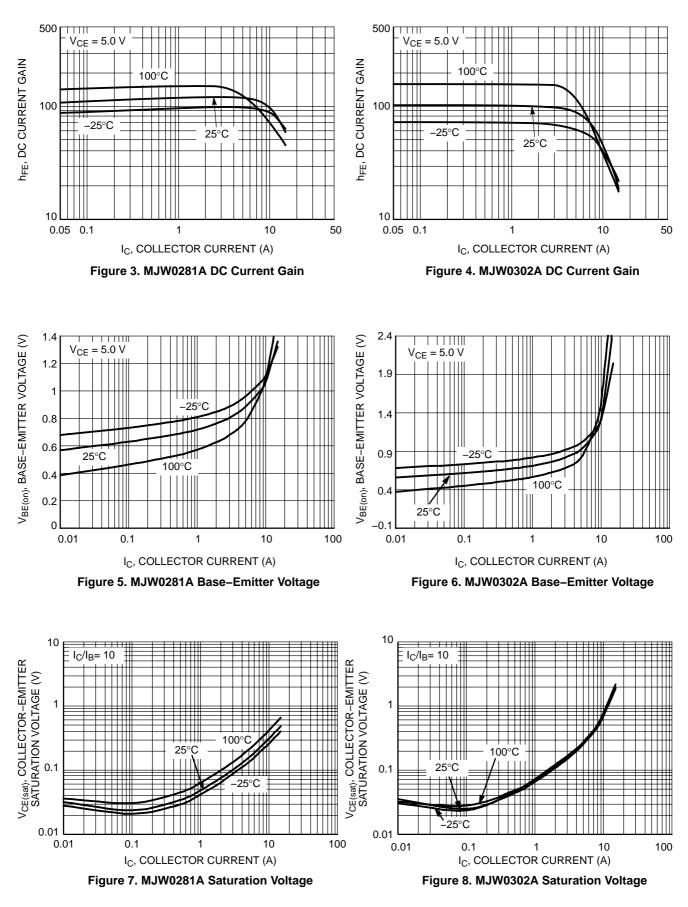
#### THERMAL CHARACTERISTICS

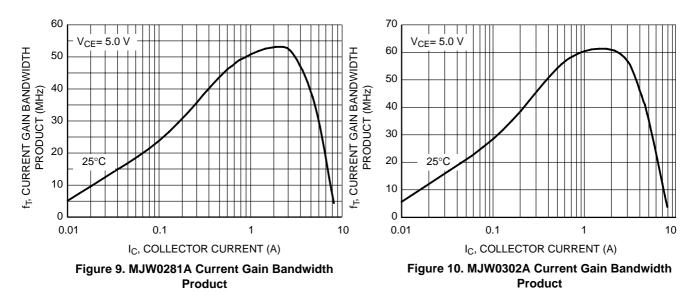
Characteristic		Value	Unit
Thermal Resistance, Junction-to-Case		0.83	°C/W

#### **ELECTRICAL CHARACTERISTICS** (T<sub>C</sub> = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector–Emitter Sustaining Voltage $(I_C = 30 \text{ mA}, I_B = 0)$	V <sub>CEO(sus)</sub>	260	-	V
Collector Cutoff Current ( $V_{CB} = 260 \text{ V}, I_E = 0$ )	Ісво	_	10	μΑ
Emitter Cutoff Current ( $V_{EB} = 5.0 \text{ V}, I_C = 0$ )	I <sub>EBO</sub>	_	5.0	μΑ
ON CHARACTERISTICS				
DC Current Gain $(I_C = 0.5 \text{ A}, V_{CE} = 5.0 \text{ V})$ $(I_C = 1.0 \text{ A}, V_{CE} = 5.0 \text{ V})$ $(I_C = 3.0 \text{ A}, V_{CE} = 5.0 \text{ V})$	h <sub>FE</sub>	75 75 75	150 150 150	-
Collector–Emitter Saturation Voltage $(I_C = 5.0 \text{ A}, I_B = 0.5 \text{ A})$	V <sub>CE(sat)</sub>	_	1.0	V
Base–Emitter On Voltage $(I_C = 5.0 \text{ A}, V_{CE} = 5.0 \text{ V})$	V <sub>BE(on)</sub>	_	1.2	V
DYNAMIC CHARACTERISTICS				
Current–Gain – Bandwidth Product ( $I_C = 1.0 \text{ A}, V_{CE} = 5.0 \text{ V}, f_{test} = 1.0 \text{ MHz}$ )	f <sub>T</sub>	30	-	MHz
Output Capacitance $(V_{CB} = 10 \text{ V}, I_E = 0, f_{test} = 1.0 \text{ MHz})$	C <sub>ob</sub>	_	400	pF

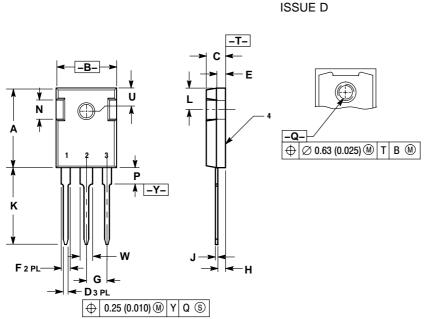






## PACKAGE DIMENSIONS

TO-247 CASE 340L-02



NOTES: 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. 2. CONTROLLING DIMENSION: MILLIMETER.

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
Α	20.32	21.08	0.800	8.30
В	15.75	16.26	0.620	0.640
C	4.70	5.30	0.185	0.209
D	1.00	1.40	0.040	0.055
Е	2.20	2.60	0.087	0.102
F	1.65	2.13	0.065	0.084
G	5.45	BSC	0.215	BSC
Н	1.50	2.49	0.059	0.098
J	0.40	0.80	0.016	0.031
K	20.06	20.83	0.790	0.820
L	5.40	6.20	0.212	0.244
N	4.32	5.49	0.170	0.216
Ρ		4.50		0.177
Q	3.55	3.65	0.140	0.144
U	6.15 BSC		0.242 BSC	
W	2.87	3.12	0.113	0.123

STYLE 3: PIN 1. BASE 2. COLLECTOR 3. EMITTER 4. COLLECTOR

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